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PATENT NUMBER and  
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM 10024475	FILING DATE 12/21/2001	CLASS 281	SUBCLASS 2811	GAU 2811	EXAMINER Im
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**\*\*APPLICANTS:** Park Chan-ho;

**\*\*CONTINUING DATA VERIFIED:**

**\*\* FOREIGN APPLICATIONS VERIFIED:**  
REPUBLIC OF KOREA 01-2166 01/15/2001

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed <input type="checkbox"/> yes <input type="checkbox"/> no		ATTORNEY DOCKET NO
35 USC 119 conditions met <input type="checkbox"/> yes <input type="checkbox"/> no		1751-294
Verified and Acknowledged Examiners's initials		
TITLE : High voltage semiconductor device having high breakdown voltage and method of fabricating the same		

U.S. DEPT. OF COMM. PAT. & TM. PTO-432L/Rev. 12-94

<b>NOTICE OF ALLOWANCE MAILED</b>		<b>CLAIMS ALLOWED</b>	
		Total Claims	Print Claim for O.G.
<b>ISSUE FEE</b>		<b>DRAWING</b>	
Amount Due	Date Paid	Sheets Drwg.	Figs. Drwg. Print Fig.
<input type="checkbox"/> <b>TERMINAL DISCLAIMER</b>		Application Examiner	
		<b>PREPARED FOR ISSUE</b> <b>WARNING:</b> The information disclosed herein may be restricted. Unauthorized disclosure may be prohibited by the United States Code Title 35, Sections 122, 181 and 368, Possession outside the U.S. Patent & Trademark Office is restricted to authorized employees and contractors only.	

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